Toshio Kamiya

List of Publications by Year in Descending Order

236 papers	27,342 citations	74 h-index	163 g-index
249 ext. papers	29,538 ext. citations	4 avg, IF	6.9 L-index

#	Paper	IF	Citations
236	Widely bandgap tunable amorphous CdGaO oxide semiconductors exhibiting electron mobilities 10 cm2 V1 s1. *Applied Physics Letters*, **2015**, 106, 082106	3.4	13
235	Vortex Pinning Properties of Phosphorous-Doped $hbox{BaFe}_{2}hbox{As}_{2}$ Epitaxial Films: Comparison Between $(hbox{La},hbox{Sr})(hbox{Al},hbox{Ta})hbox{O}_{3} $ and MgO Substrates. *IEEE Transactions on Applied Superconductivity*, **2015**, 25, 1-5	1.8	6
234	Analysis of various types of single-polypeptide-chain (sc) heterodimeric AR/DR complexes and their allosteric receptor-receptor interactions. *Biochemical and Biophysical Research Communications*, **2015**, 456, 573-9	3.4	0
233	Growth of high-quality SnS epitaxial films by H2S flow pulsed laser deposition. *Applied Physics Letters*, **2014**, 104, 072106	3.4	27
232	Positive Gate Bias Instability Induced by Diffusion of Neutral Hydrogen in Amorphous In-Ga-Zn-O Thin-Film Transistor. *IEEE Electron Device Letters*, **2014**, 35, 832-834	4.4	20
231	Two-Dimensional Transition-Metal Electride Y2C. *Chemistry of Materials*, **2014**, 26, 6638-6643	9.6	113
230	Narrow bandgap in BaZnAs and its chemical origins. *Journal of the American Chemical Society*, **2014**, 136, 14959-65	16.4	25
229	Growth of c-axis-oriented superconducting KFeAs thin films. *ACS Applied Materials & Interfaces*, **2014**, 6, 14293-301	9.5	11
228	Epitaxial growth and electronic structure of a layered zinc pnictide semiconductor, BaZn2As2. *Thin Solid Films*, **2014**, 559, 100-104	2.2	10
227	Fabrication and characterization of ZnS:(Cu,Al) thin film phosphors on glass substrates by pulsed laser deposition. *Thin Solid Films*, **2014**, 559, 18-22	2.2	10
226	Electric double-layer transistor using layered iron selenide Mott insulator TlFe1.6Se2. *Proceedings of the National Academy of Sciences of the United States of America*, **2014**, 111, 3979-83	11.5	26
225	. *Journal of Display Technology*, **2014**, 10, 979-983		15
224	High critical-current density with less anisotropy in BaFe2(As,P)2 epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. *Applied Physics Letters*, **2014**, 104, 182603	3.4	41
223	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3085-Q3090	2	43
222	. *Journal of Display Technology*, **2014**, 10, 975-978		12
221	Critical factor for epitaxial growth of cobalt-doped BaFe2As2 films by pulsed laser deposition. *Applied Physics Letters*, **2014**, 104, 172602	3.4	22
220	Superconductivity in noncentrosymmetric ternary equiatomic pnictides LaMP (M = Ir and Rh; P = P and As). *Physical Review B*, **2014**, 89,	3.3	32

219	Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass. *ECS Journal of Solid State Science and Technology*, **2014**, 3, Q3040-Q3044	2	28
218	Mobility- and temperature-dependent device model for amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2014**, 559, 40-43	2.2	30
217	Unusual pressure effects on the superconductivity of indirectly electron-doped (Ba1xLax)Fe2As2 epitaxial films. *Physical Review B*, **2013**, 88,	3.3	16
216	Superconducting Properties and Phase Diagram of Indirectly Electron-Doped $(hbox{Sr}_{1 - x}hbox{La}_{x})hbox{Fe}_{2}hbox{As}_{2}$ Epitaxial Films Grown by Pulsed Laser Deposition. *IEEE Transactions on Applied Superconductivity*, **2013**, 23, 7300405-7300405	1.8	13
215	Surface reactivity and oxygen migration in amorphous indium-gallium-zinc oxide films annealed in humid atmosphere. *Applied Physics Letters*, **2013**, 103, 201904	3.4	26
214	Magnetic structure and electromagnetic properties of LnCrAsO with a ZrCuSiAs-type structure (Ln = La, Ce, Pr, and Nd). *Inorganic Chemistry*, **2013**, 52, 13363-8	5.1	23
213	Magnetic scattering and electron pair breaking by rare-earth-ion substitution in BaFe2As2epitaxial films. *New Journal of Physics*, **2013**, 15, 073019	2.9	18
212	Effects of Diffusion of Hydrogen and Oxygen on Electrical Properties of Amorphous Oxide Semiconductor, In-Ga-Zn-O. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P5-P8	2	152
211	Anomalous scaling behavior in a mixed-state Hall effect of a cobalt-doped BaFe2As2 epitaxial film with a high critical current density over 1 MA/cm2. *Physical Review B*, **2013**, 87,	3.3	14
210	P.3: 3-D Stacked Complementary TFT Devices using n-type GZO and p-type F8T2 TFTs Operation Confirmation of NOT and NAND Logic Circuits *Digest of Technical Papers SID International Symposium*, **2013**, 44, 995-998	0.5	1
209	4.1: Invited Paper: Electronic Structure, Carrier Transport, Defects and Impurities in Amorphous Oxide Semiconductor. *Digest of Technical Papers SID International Symposium*, **2013**, 44, 11-13	0.5	3
208	P.142L: Late-News Poster: Electron Injecting Material for OLEDs driven by Oxide TFTs: Amorphous C12A7 Electride. *Digest of Technical Papers SID International Symposium*, **2013**, 44, 1473-1476	0.5	6
207	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2013**, 103, 202114	3.4	92
206	Apparent high mobility ~30 cm2/Vs of amorphous InGaZnO thin-film transistor and its origin. *Journal of the Ceramic Society of Japan*, **2013**, 121, 295-298	1	4
205	Microstructure and transport properties of [001]-tilt bicrystal grain boundaries in iron pnictide superconductor, cobalt-doped BaFe2As2. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2012**, 177, 515-519	3.1	32
204	Superconducting compounds with metallic square net. *Solid State Communications*, **2012**, 152, 666-670	1.6	6
203	Operation model with carrier-density dependent mobility for amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2012**, 520, 3791-3795	2.2	11
202	Effects of low-temperature ozone annealing on operation characteristics of amorphous InGaZnO thin-film transistors. *Thin Solid Films*, **2012**, 520, 3787-3790	2.2	30

201	Photovoltaic properties of n-type amorphous InGaZnO and p-type single crystal Si heterojunction solar cells: Effects of Ga content. *Thin Solid Films*, **2012**, 520, 3808-3812	2.2	18
200	Stability and high-frequency operation of amorphous InGaZnO thin-film transistors with various passivation layers. *Thin Solid Films*, **2012**, 520, 3778-3782	2.2	69
199	Amorphous InGaZnO Dual-Gate TFTs: CurrentVoltage Characteristics and Electrical Stress Instabilities. *IEEE Transactions on Electron Devices*, **2012**, 59, 1928-1935	2.9	40
198	Doping effects in amorphous oxides. *Journal of the Ceramic Society of Japan*, **2012**, 120, 447-457	1	30
197	Optical evidence for quantization in transparent amorphous oxide semiconductor superlattice. *Physical Review B*, **2012**, 86,	3.3	18
196	Band alignment of InGaZnO4/Si interface by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2012**, 112, 033713	2.5	33
195	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. *Journal of Applied Physics*, **2012**, 111, 073513	2.5	74
194	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. *Journal of the Physical Society of Japan*, **2012**, 81, 011011	1.5	47
193	Maximum applied voltage detector using amorphous InGaZnO thin-film transistor exposed to ozone annealing. *Solid-State Electronics*, **2012**, 75, 74-76	1.7	4
192	Electron injection barriers between air-stable electride with low work function, C12A7:e and pentacene, C60 and copper phthalocyanine. *Journal of Materials Chemistry*, **2012**, 22, 4278		21
191	Light Irradiation History Sensor Using Amorphous In-Ga-Zn-O Thin-Film Transistor Exposed to Ozone Annealing. *IEEE Electron Device Letters*, **2012**, 33, 384-386	4.4	6
190	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe1xCox)2As2(AE=alkaline earth). *Superconductor Science and Technology*, **2012**, 25, 084015	3.1	41
189	Identical effects of indirect and direct electron doping of superconducting BaFe2As2 thin films. *Physical Review B*, **2012**, 85,	3.3	41
188	Highly stable amorphous In-Ga-Zn-O thin-film transistors produced by eliminating deep subgap defects. *Applied Physics Letters*, **2011**, 99, 053505	3.4	139
187	Effects of excess oxygen on operation characteristics of amorphous In-Ga-Zn-O thin-film transistors. *Applied Physics Letters*, **2011**, 99, 093507	3.4	166
186	Bipolar Conduction in SnO Thin Films. *Electrochemical and Solid-State Letters*, **2011**, 14, H13		132
185	Advantageous grain boundaries in iron pnictide superconductors. *Nature Communications*, **2011**, 2, 409	17.4	212
184	A germanate transparent conductive oxide. *Nature Communications*, **2011**, 2, 470	17.4	75

183	Simple Analytical Model of On Operation of Amorphous InGaZnO Thin-Film Transistors. *IEEE Transactions on Electron Devices*, **2011**, 58, 3463-3471	2.9	47
182	Solid-phase epitaxial growth of (111)-oriented Si film on InGaO3(ZnO)5 buffer layer. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 920-923	2.1	
181	Excimer laser crystallization of InGaZnO4 on SiO2 substrate. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 1694-1696	2.1	6
180	Ambipolar oxide thin-film transistor. *Advanced Materials*, **2011**, 23, 3431-4	24	207
179	LaCo2B2: a Co-based layered superconductor with a ThCr2Si2-type structure. *Physical Review Letters*, **2011**, 106, 237001	7.4	29
178	. *IEEE Electron Device Letters*, **2011**, 32, 1695-1697	4.4	69
177	Depth analysis of subgap electronic states in amorphous oxide semiconductor, a-In-Ga-Zn-O, studied by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2011**, 109, 073726	2.5	141
176	Biaxially textured cobalt-doped BaFe2As2 films with high critical current density over 1 MA/cm2 on MgO-buffered metal-tape flexible substrates. *Applied Physics Letters*, **2011**, 98, 242510	3.4	105
175	New functionalities in abundant element oxides: ubiquitous element strategy. *Science and Technology of Advanced Materials*, **2011**, 12, 034303	7.1	30
174	Electronic Structure and Photovoltaic Properties of n-Type Amorphous In-Ga-Zn-O and p-Type Single Crystal Si Heterojunctions. *Electrochemical and Solid-State Letters*, **2011**, 14, H346		10
173	Operation Characteristics of Thin-Film Transistors Using Very Thin Amorphous InGaZnO Channels. *Electrochemical and Solid-State Letters*, **2011**, 14, H197		43
172	Josephson junction in cobalt-doped BaFe2As2 epitaxial thin films on (La,Sr)(Al,Ta)O3 bicrystal substrates. *Applied Physics Letters*, **2010**, 96, 142507	3.4	66
171	Large Photoresponse in Amorphous InGaZnO and Origin of Reversible and Slow Decay. *Electrochemical and Solid-State Letters*, **2010**, 13, H324		54
170	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. *Applied Physics Letters*, **2010**, 97, 072111	3.4	165
169	Three-dimensionally stacked flexible integrated circuit: Amorphous oxide/polymer hybrid complementary inverter using n-type a-InGaZnO and p-type poly-(9,9-dioctylfluorene-co-bithiophene) thin-film transistors. *Applied Physics Letters*, **2010**, 96, 263509	3.4	81
168	Intrinsic carrier mobility in amorphous InGaZnO thin-film transistors determined by combined field-effect technique. *Applied Physics Letters*, **2010**, 96, 262105	3.4	48
167	Origins of hole doping and relevant optoelectronic properties of wide gap p-type semiconductor, LaCuOSe. *Journal of the American Chemical Society*, **2010**, 132, 15060-7	16.4	36
166	Present status of amorphous In-Ga-Zn-O thin-film transistors. *Science and Technology of Advanced Materials*, **2010**, 11, 044305	7.1	1287

165	Fabrication of Atomically Flat ScAlMgO4 Epitaxial Buffer Layer and Low-Temperature Growth of High-Mobility ZnO Films. *Crystal Growth and Design*, **2010**, 10, 1084-1089	3.5	5
164	Material characteristics and applications of transparent amorphous oxide semiconductors. *NPG Asia Materials*, **2010**, 2, 15-22	10.3	664
163	Origin of definite Hall voltage and positive slope in mobility-donor density relation in disordered oxide semiconductors. *Applied Physics Letters*, **2010**, 96, 122103	3.4	121
162	High Critical Current Density 4 MA/cm2in Co-Doped BaFe2As2Epitaxial Films Grown on (La,Sr)(Al,Ta)O3Substrates without Buffer Layers. *Applied Physics Express*, **2010**, 3, 063101	2.4	81
161	Fabrication and electron transport properties of epitaxial films of electron-doped 12CaO·7Al2O3 and 12SrO·7Al2O3. *Journal of Solid State Chemistry*, **2010**, 183, 385-391	3.3	17
160	Electrical and magnetic properties of quaternary compounds LnMnPO (Ln=Nd, Sm, Gd) with ZrCuSiAs-type structure. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 47-50	3.1	7
159	Breast cancer stem cells. *Breast Cancer*, **2010**, 17, 80-5	3.4	70
158	Impurities in FeAs-based superconductor, SrFe2As2, studied by first-principles calculations. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 244-247	3.1	4
157	Electronic structures of MnP-based crystals: LaMnOP, BaMn2P2, and KMnP. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2010**, 173, 239-243	3.1	6
156	Comprehensive studies on the stabilities of a-In-Ga-Zn-O based thin film transistor by constant current stress. *Thin Solid Films*, **2010**, 518, 3012-3016	2.2	45
155	Steady-state photoconductivity of amorphous InGaZnO. *Thin Solid Films*, **2010**, 518, 3000-3003	2.2	16
154	Fabrication of GaN epitaxial thin film on InGaZnO4 single-crystalline buffer layer. *Thin Solid Films*, **2010**, 518, 2996-2999	2.2	3
153	Device characteristics improvement of a-InGaZnO TFTs by low-temperature annealing. *Thin Solid Films*, **2010**, 518, 3017-3021	2.2	80
152	Origin of high-density hole doping and anisotropic hole transport in a wide gap layered semiconductor LaCuOSe studied by first-principles calculations. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1636-1641	1.6	6
151	Subgap states, doping and defect formation energies in amorphous oxide semiconductor a-InGaZnO4 studied by density functional theory. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1698-1703	1.6	127
150	Water-induced superconductivity in SrFe2As2. *Physical Review B*, **2009**, 80,	3.3	64
149	First-principles study of native point defects in crystalline indium gallium zinc oxide. *Journal of Applied Physics*, **2009**, 105, 093712	2.5	65
148	Amorphous InGaZnO coplanar homojunction thin-film transistor. *Applied Physics Letters*, **2009**, 94, 133502	3.4	150

147	Humidity-Sensitive Electrical Conductivity in Ca[sub 12]Al[sub 14]Si[sub x]O[sub 32]Cl[sub 2+x] (0≤x≤3.4) Ceramics. *Electrochemical and Solid-State Letters*, **2009**, 12, J11		11
146	Origins of threshold voltage shifts in room-temperature deposited and annealed a-InGaZnO thin-film transistors. *Applied Physics Letters*, **2009**, 95, 013502	3.4	295
145	Large domain growth of GaN epitaxial films on lattice-matched buffer layer ScAlMgO4. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2009**, 161, 66-70	3.1	5
144	Electronic structure of the amorphous oxide semiconductor a-InGaZnO4x : Tauc-Lorentz optical model and origins of subgap states. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 860-867	1.6	183
143	Tin monoxide as an s-orbital-based p-type oxide semiconductor: Electronic structures and TFT application. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 2187-2191	1.6	185
142	Effects of post-annealing on (110) Cu2O epitaxial films and origin of low mobility in Cu2O thin-film transistor. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 2192-2197	1.6	59
141	Bistable resistance switching in surface-oxidized C12A7:e- single-crystal. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2009**, 161, 76-79	3.1	16
140	Amorphous InGaZn-O thin-film transistor with coplanar homojunction structure. *Thin Solid Films*, **2009**, 518, 1309-1313	2.2	50
139	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped BaFe2As2. *Solid State Communications*, **2009**, 149, 2121-2124	1.6	65
138	Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application. *Journal of the European Ceramic Society*, **2009**, 29, 245-253	6	17
137	Heteroepitaxial film growth of layered compounds with the ZrCuSiAs-type and ThCr2Si2-type structures: From Cu-based semiconductors to Fe-based superconductors. *Physica C: Superconductivity and Its Applications*, **2009**, 469, 657-666	1.3	37
136	Origins of High Mobility and Low Operation Voltage of Amorphous Oxide TFTs: Electronic Structure, Electron Transport, Defects and Doping. *Journal of Display Technology*, **2009**, 5, 273-288		371
135	Electronic Structures Above Mobility Edges in Crystalline and Amorphous In-Ga-Zn-O: Percolation Conduction Examined by Analytical Model. *Journal of Display Technology*, **2009**, 5, 462-467		185
134	Antiferromagnetic bipolar semiconductor LaMnPO with ZrCuSiAs-type structure. *Journal of Applied Physics*, **2009**, 105, 093916	2.5	44
133	Low Threshold Voltage and Carrier Injection Properties of Inverted Organic Light-Emitting Diodes with [Ca24Al28O64]4+(4e-)Cathode and Cu2-xSe Anode. *Journal of Physical Chemistry C*, **2009**, 113, 18379-18384	3.8	42
132	Epitaxial film growth and optoelectrical properties of layered semiconductors, LaMnXO (X=P, As, and Sb). *Journal of Applied Physics*, **2009**, 105, 073903	2.5	30
131	Trap densities in amorphous-InGaZnO4 thin-film transistors. *Applied Physics Letters*, **2008**, 92, 133512	3.4	254
130	Solid State Syntheses of 12SrO·7Al2O3 and Formation of High Density Oxygen Radical Anions, O- and O2- *Chemistry of Materials*, **2008**, 20, 5987-5996	9.6	27

129	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M3+ Ions. *Chemistry of Materials*, **2008**, 20, 326-334	9.6	227
128	Localized and Delocalized Electrons in Room-Temperature Stable Electride [Ca24Al28O64]4+(O2-)2-x(e-)2x: Analysis of Optical Reflectance Spectra. *Journal of Physical Chemistry C*, **2008**, 112, 4753-4760	3.8	51
127	ZnO-Based Semiconductors as Building Blocks for Active Devices. *MRS Bulletin*, **2008**, 33, 1061-1066	3.2	41
126	Thin film and bulk fabrication of room-temperature-stable electride C12A7:e□utilizing reduced amorphous 12CaO□7Al2O3(C12A7). *Journal of Non-Crystalline Solids*, **2008**, 354, 2772-2776	3.9	23
125	Factors controlling electron transport properties in transparent amorphous oxide semiconductors. *Journal of Non-Crystalline Solids*, **2008**, 354, 2796-2800	3.9	152
124	p-channel thin-film transistor using p-type oxide semiconductor, SnO. *Applied Physics Letters*, **2008**, 93, 032113	3.4	491
123	Modeling of amorphous InGaZnO4 thin film transistors and their subgap density of states. *Applied Physics Letters*, **2008**, 92, 133503	3.4	289
122	Electromagnetic properties and electronic structure of the iron-based layered superconductor LaFePO. *Physical Review B*, **2008**, 77,	3.3	68
121	Optical and electrical properties of amorphous zinc tin oxide thin films examined for thin film transistor application. *Journal of Vacuum Science & Technology B*, **2008**, 26, 495		89
120	Epitaxial growth of high mobility Cu2O thin films and application to p-channel thin film transistor. *Applied Physics Letters*, **2008**, 93, 202107	3.4	193
119	Superconductivity in Epitaxial Thin Films of Co-Doped SrFe2As2with Bilayered FeAs Structures and their Magnetic Anisotropy. *Applied Physics Express*, **2008**, 1, 101702	2.4	101
118	Optical and Carrier Transport Properties of Cosputtered Zn□In□Sn□O Films and Their Applications to TFTs. *Journal of the Electrochemical Society*, **2008**, 155, H390	3.9	57
117	Subgap states in transparent amorphous oxide semiconductor, In□Ga□Zn□O, observed by bulk sensitive x-ray photoelectron spectroscopy. *Applied Physics Letters*, **2008**, 92, 202117	3.4	268
116	Itinerant ferromagnetism in the layered crystals LaCoOX(X=P,As). *Physical Review B*, **2008**, 77,	3.3	129
115	Defect passivation and homogenization of amorphous oxide thin-film transistor by wet O2 annealing. *Applied Physics Letters*, **2008**, 93, 192107	3.4	243
114	Characterization of copper selenide thin film hole-injection layers deposited at room temperature for use with p-type organic semiconductors. *Journal of Applied Physics*, **2008**, 104, 113723	2.5	14
113	Heteroepitaxial growth and optoelectronic properties of layered iron oxyarsenide, LaFeAsO. *Applied Physics Letters*, **2008**, 93, 162504	3.4	88
112	Amorphous oxide channel TFTs. *Thin Solid Films*, **2008**, 516, 1516-1522	2.2	155

111	Heteroepitaxial growth of layered semiconductors, LaZnOPn (Pn = P and As). *Thin Solid Films*, **2008**, 516, 5800-5804	2.2	36
110	Specific contact resistances between amorphous oxide semiconductor InGaZnO and metallic electrodes. *Thin Solid Films*, **2008**, 516, 5899-5902	2.2	171
109	Control of carrier concentration and surface flattening of CuGaO2 epitaxial films for a p-channel transparent transistor. *Thin Solid Films*, **2008**, 516, 5790-5794	2.2	32
108	Electronic structure of oxygen deficient amorphous oxide semiconductor a-InGaZnO4 : Optical analyses and first-principle calculations. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3098-3100		187
107	Electrical and optical properties of copper-based chalcogenide thin films deposited by pulsed laser deposition at room temperature: Toward p-channel thin film transistor fabricable at room temperature. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 2007-2012	1.6	5
106	Amorphous SnGaZnO channel thin-film transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 1920-1924	1.6	34
105	Low and small resistance hole-injection barrier for NPB realized by wide-gap p-type degenerate semiconductor, LaCuOSe:Mg. *Organic Electronics*, **2008**, 9, 890-894	3.5	28
104	Nickel-based layered superconductor, LaNiOAs. *Journal of Solid State Chemistry*, **2008**, 181, 2117-2120	3.3	86
103	Electronic and magnetic properties of layered LnFePO (Ln=La and Ce). *Journal of Physics and Chemistry of Solids*, **2008**, 69, 2916-2918	3.9	13
102	Nickel-based phosphide superconductor with infinite-layer structure, BaNi2P2. *Solid State Communications*, **2008**, 147, 111-113	1.6	110
101	Fabrication of ScAlMgO4 epitaxial thin films using ScGaO3(ZnO)m buffer layers and its application to lattice-matched buffer layer for ZnO epitaxial growth. *Thin Solid Films*, **2008**, 516, 5842-5846	2.2	4
100	Apparent bipolarity and Seebeck sign inversion in a layered semiconductor: LaZnOP. *Physical Review B*, **2007**, 76,	3.3	27
99	Metallic state in a lime-alumina compound with nanoporous structure. *Nano Letters*, **2007**, 7, 1138-43	11.5	183
98	Local coordination structure and electronic structure of the large electron mobility amorphous oxide semiconductor In-Ga-Zn-O: Experiment and ab initio calculations. *Physical Review B*, **2007**, 75,	3.3	252
97	Structural and photo-induced properties of Eu2+-doped Ca2ZnSi2O7: A red phosphor for white light generation by blue ray excitation. *Journal of Luminescence*, **2007**, 122-123, 339-341	3.8	17
96	Optoelectronic properties and electronic structure of YCuOSe. *Journal of Applied Physics*, **2007**, 102, 113714	2.5	18
95	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. *Applied Physics Letters*, **2007**, 91, 012104	3.4	82
94	Fast Thin-Film Transistor Circuits Based on Amorphous Oxide Semiconductor. *IEEE Electron Device Letters*, **2007**, 28, 273-275	4.4	104

93	Development of latent images due to transient free carrier electrons by femtosecond laser pulses and its application to grating shape trimming. *Applied Physics Letters*, **2007**, 90, 011107	3.4	4
92	Sn[sub 0.9]In[sub 0.1]P[sub 2]O[sub 7]-Based Organic/Inorganic Composite Membranes. *Journal of the Electrochemical Society*, **2007**, 154, B63	3.9	33
91	Novel Room Temperature Stable Electride 12SrO 7Al2O3 Thin Films: Fabrication, Optical and Electron Transport Properties. *Journal of the Ceramic Society of Japan*, **2007**, 115, 567-570	1	19
90	Anion Incorporation-induced Cage Deformation in 12CaO·7Al2O3Crystal. *Chemistry Letters*, **2007**, 36, 902-903	1.7	22
89	Combinatorial approach to thin-film transistors using multicomponent semiconductor channels: An application to amorphous oxide semiconductors in In□Ga□Zn□O system. *Applied Physics Letters*, **2007**, 90, 242114	3.4	200
88	High electron doping to a wide band gap semiconductor 12CaO·7Al2O3 thin film. *Applied Physics Letters*, **2007**, 90, 182105	3.4	48
87	Epitaxial film growth, optical, electrical, and magnetic properties of layered oxide In3FeTi2O10. *Journal of Applied Physics*, **2007**, 101, 103714	2.5	6
86	Intermediate-Temperature Proton Conduction in Al[sup 3+]-Doped SnP[sub 2]O[sub 7]. *Journal of the Electrochemical Society*, **2007**, 154, B1265	3.9	81
85	Photoelectron Spectroscopic Study of C12A7:e- and Alq3 Interface: The Formation of a Low Electron-Injection Barrier. *Journal of Physical Chemistry C*, **2007**, 111, 8403-8406	3.8	59
84	Nickel-based oxyphosphide superconductor with a layered crystal structure, LaNiOP. *Inorganic Chemistry*, **2007**, 46, 7719-21	5.1	245
83	Growth, structure and carrier transport properties of Ga2O3 epitaxial film examined for transparent field-effect transistor. *Thin Solid Films*, **2006**, 496, 37-41	2.2	142
82	Proton Conduction in In3+-doped SnP2O7 with Various P/(Sn+In) Ratios. *ECS Transactions*, **2006**, 2, 43-491		1
81	Integrated Circuits Based on Amorphous Indium-Gallium-Zinc-Oxide-Channel Thin-Film Transistors. *ECS Transactions*, **2006**, 3, 293-300	1	2
80	Photoluminescence from Au ion-implanted nanoporous single-crystal 12CaO·7Al2O3. *Physical Review B*, **2006**, 73,	3.3	39
79	Electron field emission from TiO2 nanotube arrays synthesized by hydrothermal reaction. *Applied Physics Letters*, **2006**, 89, 043114	3.4	76
78	Proton Conduction in In[sup 3+]-Doped SnP[sub 2]O[sub 7] at Intermediate Temperatures. *Journal of the Electrochemical Society*, **2006**, 153, A1604	3.9	129
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